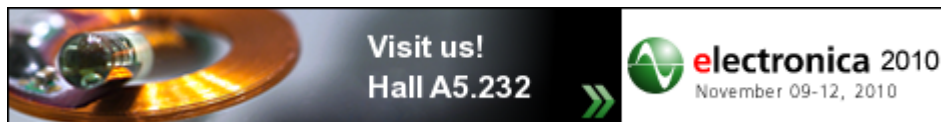


## Press Release

030e

28 October 2010



### 4 A/600V SiGaN Schottky by microGaN and Diotec

microGaN GmbH, based in Ulm/Germany, and Diotec Semiconductor AG, with headquarter in Heitersheim/Germany, are cooperating in design and marketing of Gallium Nitride (GaN) rectifier devices. One of the recent developments is a 4 Amp, 600 Volt so called "SiGaN Schottky" diode, with an ultra low barrier of 0.3 Volts. Like any Schottky diode, it has got negligible reverse recovery and only a very low switching time, caused by junction capacity. The "stored charge" is comparable to that of Silicon Carbide (SiC) devices, while the forward voltage drop is much lower: At 4 Amp and 25°C it is typically 1.2 Volts, at 100°C typically 1.6 Volts.

Such devices are ideally suited for high frequent switching circuits, such as Power Factor Correction (PFC) and inverter circuits. They boost PFC efficiency especially in partial load condition. Power losses in drive and solar inverters can be significantly reduced, just by bypassing the body diodes of Si-Superjunction MOSFETs by such high speed free-wheeling diodes.

The devices will be tested first from selected pilot customers, and are then offered to the market. For more information please visit the Diotec stand No. 232 in hall A5 during electronica in Munich.

On the web: <http://www.microgan.com/> – <http://www.diotec.com/>

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**Diotec Semiconductor AG** with headquarter in Germany and four worldwide factories produces and sells semiconductors such as Diodes, Rectifiers, Diacs and Transistors and has more than 30 years of experience.

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